

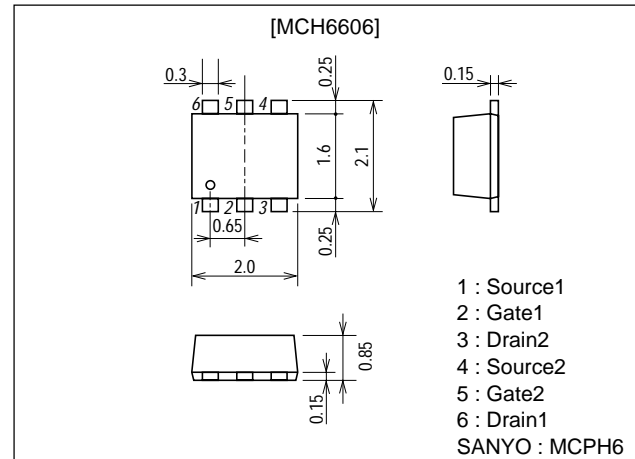
**MCH6606****Ultrahigh-Speed Switching Applications****Features**

- Low ON resistance.
- Ultrahigh-speed switching.
- 4V drive.
- Composite type with 2 MOSFETs contained in one package, facilitating high-density mounting.

**Package Dimensions**

unit:mm

2173

**Specifications****Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		50	V
Gate-to-Source Voltage	$V_{GSS}$		±20	V
Drain Current (DC)	$I_D$		0.25	A
Drain Current (pulse)	$I_{DP}$	PW≤10μs, duty cycle≤1%	1	A
Allowable Power Dissipation	$P_D$	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm) 1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

**Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0$	50			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=50V, V_{GS}=0$			10	μA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=±16V, V_{DS}=0$			±10	μA
Cutoff Voltage	$V_{GSS(off)}$	$V_{DS}=10V, I_D=100μA$	1		2.4	V
Forward Transfer Admittance	yfs	$V_{DS}=10V, I_D=50mA$	85	120		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=50mA, V_{GS}=10V$		5.8	7.5	Ω
	$R_{DS(on)2}$	$I_D=30mA, V_{GS}=4V$		7.5	10.5	Ω
Input Capacitance	Ciss	$V_{DS}=10V, f=1MHz$		6.2		pF
Output Capacitance	Coss	$V_{DS}=10V, f=1MHz$		4.4		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=10V, f=1MHz$		1.5		pF

Marking : FF

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**SANYO Electric Co.,Ltd. Semiconductor Company**

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

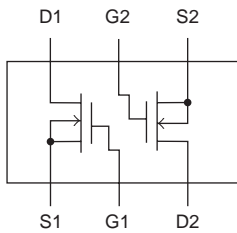
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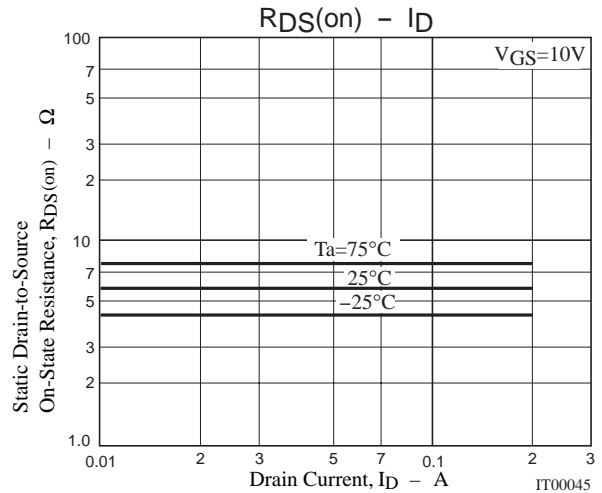
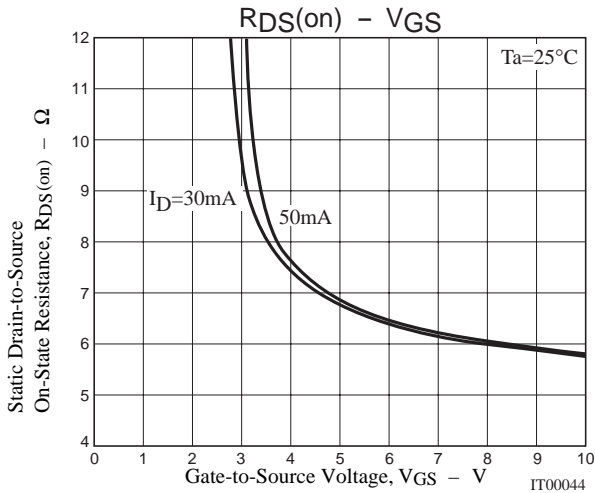
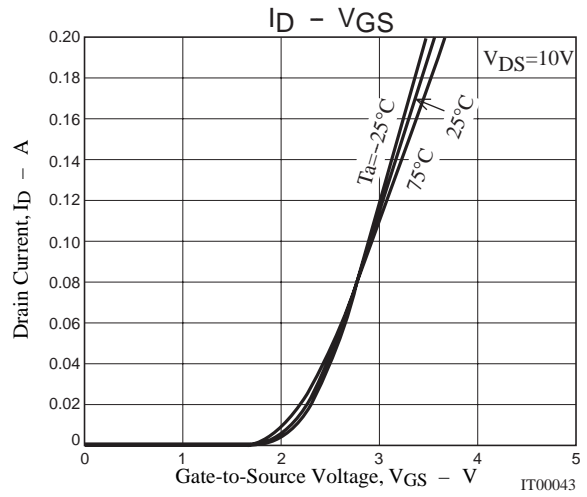
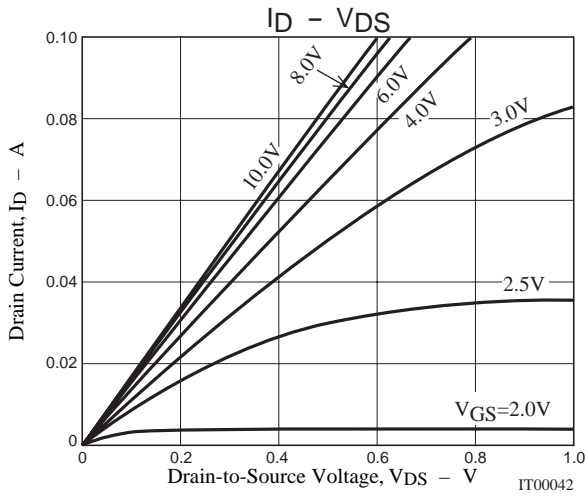
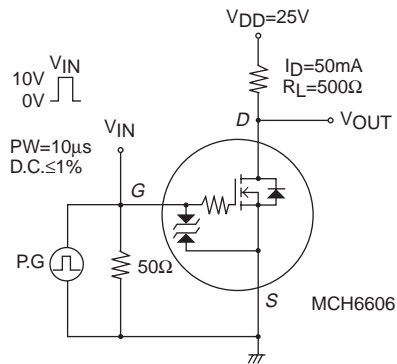
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	$t_r$	See specified Test Circuit		11		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		105		ns
Fall Time	$t_f$	See specified Test Circuit		75		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		1.40		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		0.21		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		0.34		nC
Diode Forward Voltage	$V_{SD}$	$I_S=100mA, V_{GS}=0$		0.85	1.2	V

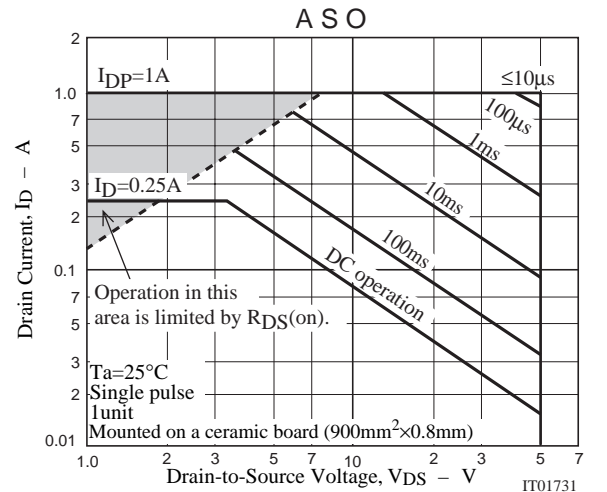
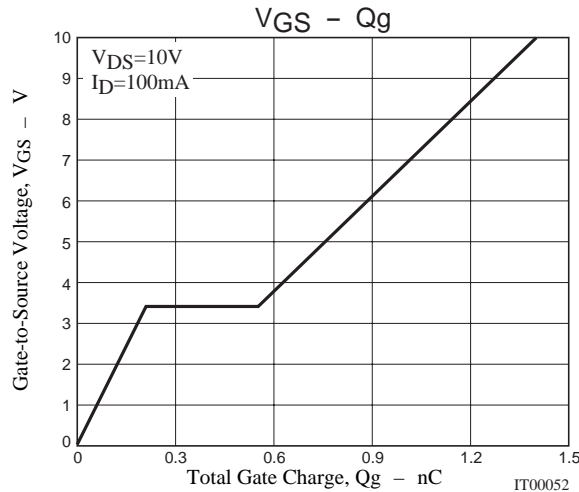
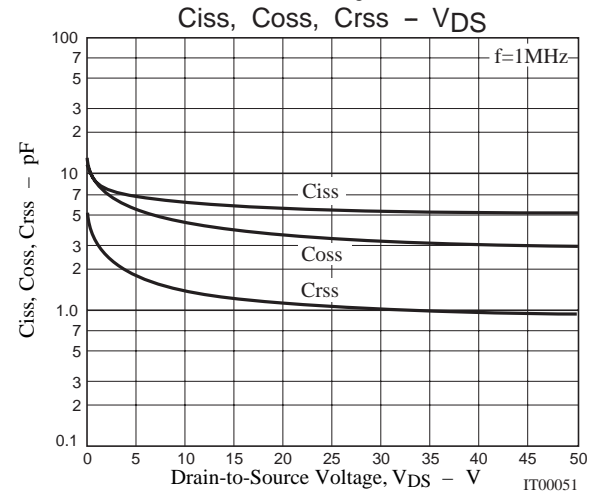
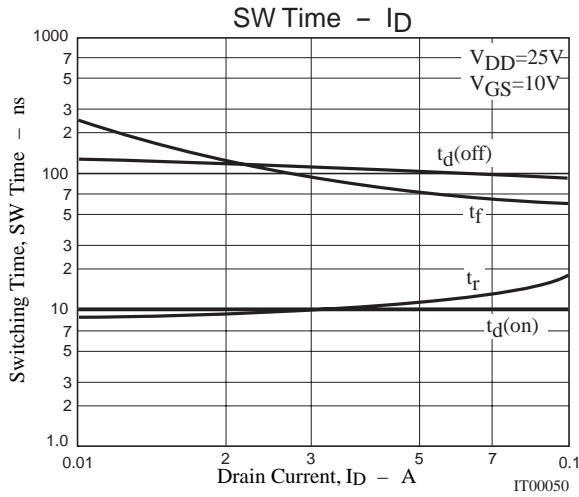
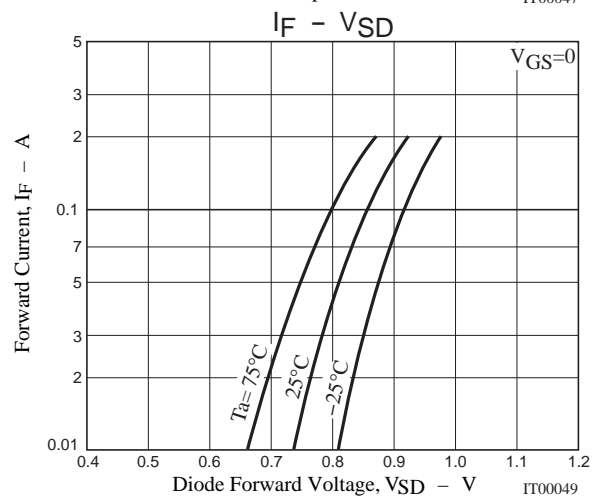
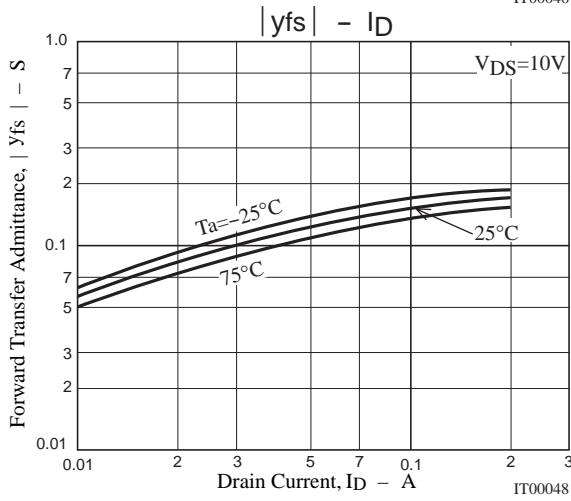
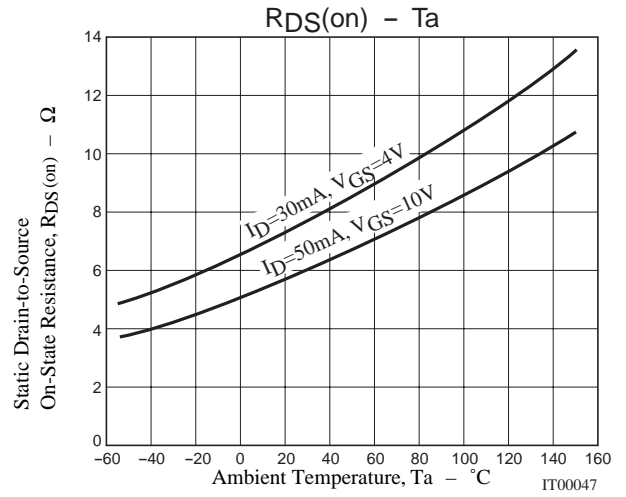
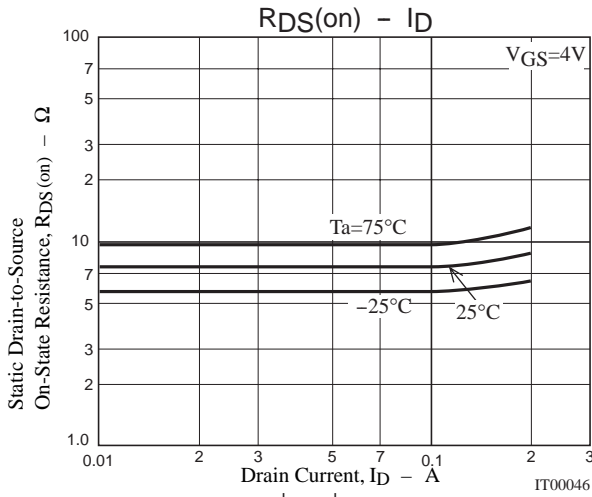
## Electrical Connection



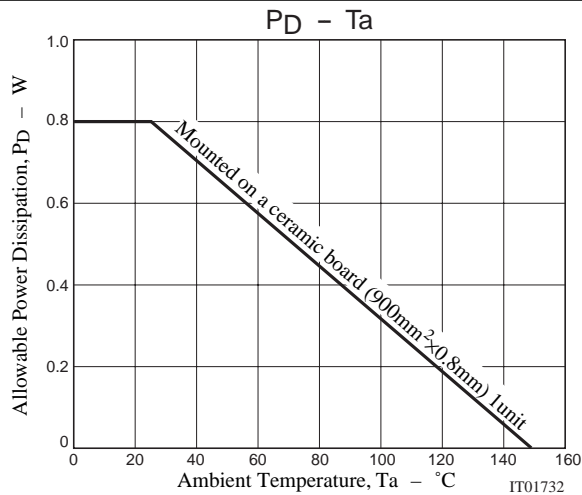
## Switching Time Test Circuit



# MCH6606



## MCH6606



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